

2SB1440

Silicon PNP epitaxial planar type

For low-frequency output amplification Complementary to 2SD2185

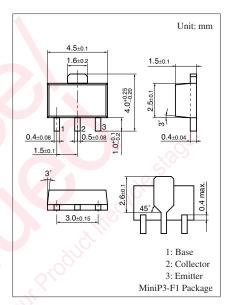
■ Features

- ullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	-50	V	
Collector-emitter voltage (Base open)	V_{CEO}	-50	V	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_{C}	-2	A	
Peak collector current	I_{CP}	-3	A	
Collector power dissipation *	P _C	1	W	
Junction temperature	T _j	150	°CO	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) *: Print circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion



Marking Symbol: 1 I

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emiter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -1 \text{ mA}, I_{\rm B} = 0$	-50			V
Emiter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = -2 \text{ V}, I_{C} = -200 \text{ mA}$	120		340	_
	h _{FE2}	$V_{CE} = -2 \text{ V}, I_{C} = -1 \text{ A}$	60			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -1 A, I_B = -50 \text{ mA}$		- 0.2	- 0.3	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = -1 A, I_B = -50 \text{ mA}$		- 0.85	-1.2	V
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		45	60	pF
(Common base, input open circuited)						

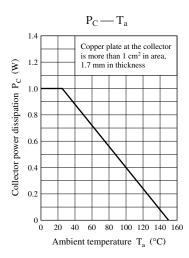
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

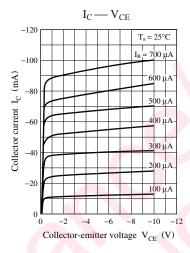
2. *1: Pulse measurement

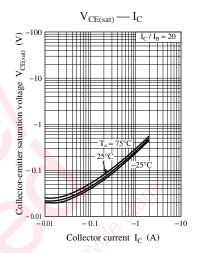
*2: Rank classification

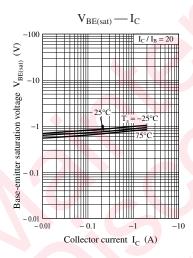
Rank	R	S
$h_{\rm FE1}$	120 to 240	170 to 340

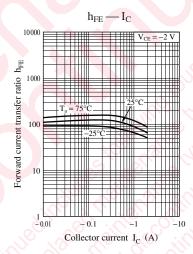
Panasonic

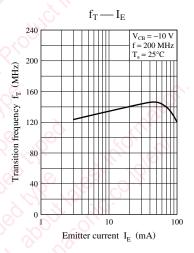


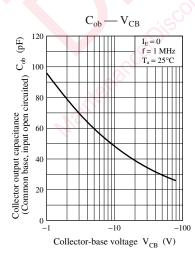












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